

BCR3PM-12LG

Triac

Medium Power Use

REJ03G1506-0100 Rev.1.00 Feb 14, 2007

Features

I_{T (RMS)}: 3 A
 V_{DRM}: 600 V

• I_{FGTI}, I_{RGTI}, I_{RGT III}: 20 mA

• V_{iso}: 2000 V

The Product guaranteed maximum junction temperature 150°C

• Insulated Type

• Planar Type

• UL Recognized : Yellow Card No. E223904

File No.E80271

Outline

RENESAS Package code: PRSS0003AA-A (Package name: TO-220F)





- 1. T₁ Terminal
- 2. T₂ Terminal
- 3. Gate Terminal

Applications

AC no junction Switching, light dimmer, electronic blanket, Control of household electrical appliance such as electric fans, solenoid driver, small motor control, and other general purpose control applications

Parameter	Svmbol	Voltage class	Unit	
Farameter	Syllibol	12	Onit	
Repetitive peak off-state voltage ^{Note1}	V_{DRM}	600	V	
Non-repetitive peak off-state voltage ^{Note1}	V_{DSM}	720	V	

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Parameter	Symbol	Ratings	Unit	Conditions
RMS on-state current	I _{T (RMS)}	3.0	Α	Commercial frequency, sine full wave
				360°conduction, Tc = 130°C
Surge on-state current	I _{TSM}	30	Α	60Hz sinewave 1 full cycle, peak value,
				non-repetitive
I ² t for fusion	l ² t	3.7	A ² s	Value corresponding to 1 cycle of half
				wave 60Hz, surge on-state current
Peak gate power dissipation	P _{GM}	5	W	
Average gate power dissipation	P _{G (AV)}	0.5	W	
Peak gate voltage	V_{GM}	10	V	
Peak gate current	I _{GM}	2	Α	
Junction Temperature	Tj	-40 to +150	°C	
Storage temperature	Tstg	-40 to +150	°C	
Mass	_	2.0	g	Typical value
Isolation voltage	V _{iso}	2000	V	Ta = 25°C, AC 1 minute,
				T ₁ • T ₂ • G terminal to case

Notes: 1. Gate open.

Electrical Characteristics

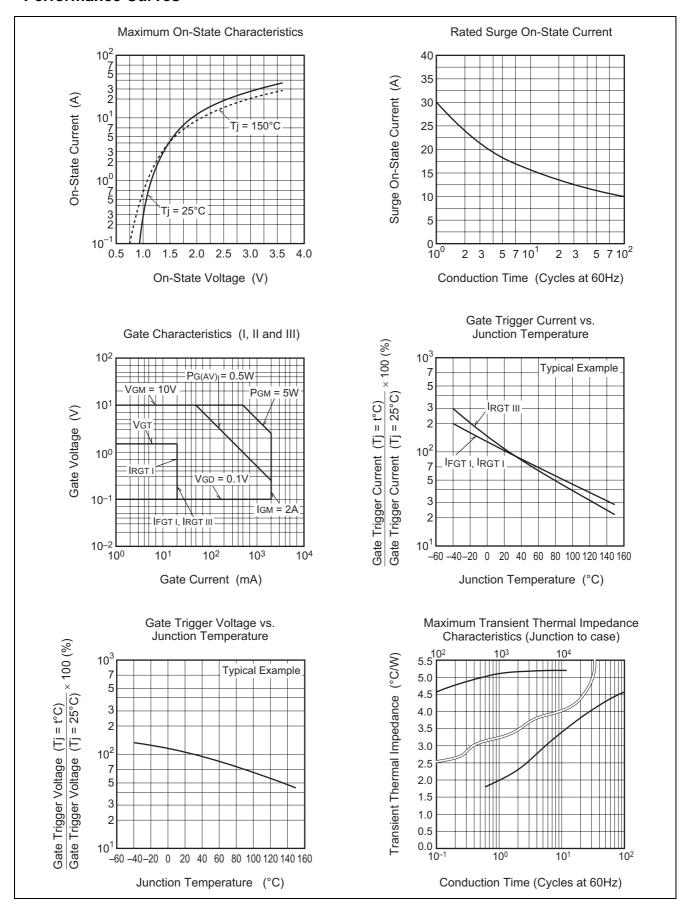
Parameter		Symbol	Min.	Тур.	Max.	Unit	Test conditions
Repetitive peak off-state current		I _{DRM}	_	_	2.0	mA	Tj = 150°C, V _{DRM} applied
On-state voltage		V_{TM}	_	_	1.5	V	Tc = 25°C, I _{TM} = 4.5 A, instantaneous measurement
Gate trigger voltage ^{Note2}	I	$V_{FGT_{\mathrm{I}}}$	_	_	1.5	V	$Tj = 25$ °C, $V_D = 6$ V, $R_L = 6$ Ω,
	II	$V_{RGT_{I}}$	_	_	1.5	V	$R_G = 330 \Omega$
	III	$V_{RGT_{III}}$	_	_	1.5	V	
Gate trigger curent ^{Note2}	I	I _{FGTI}	_	_	20	mA	$Tj = 25$ °C, $V_D = 6$ V, $R_L = 6$ Ω,
	II	I _{RGTI}	_	_	20	mA	$R_G = 330 \Omega$
	III	I _{RGTIII}	_	_	20	mA	
Gate non-trigger voltage		$V_{\sf GD}$	0.2/0.1	_	_	V	$Tj = 125$ °C/150°C, $V_D = 1/2 V_{DRM}$
Thermal resistance		R _{th (j-c)}	_	_	5.2	°C/W	Junction to case ^{Note3}
Critical-rate of rise of off-state commutation voltage ^{Note4}		(dv/dt)c	5/1	_	_	V/μs	Tj = 125°C/150°C

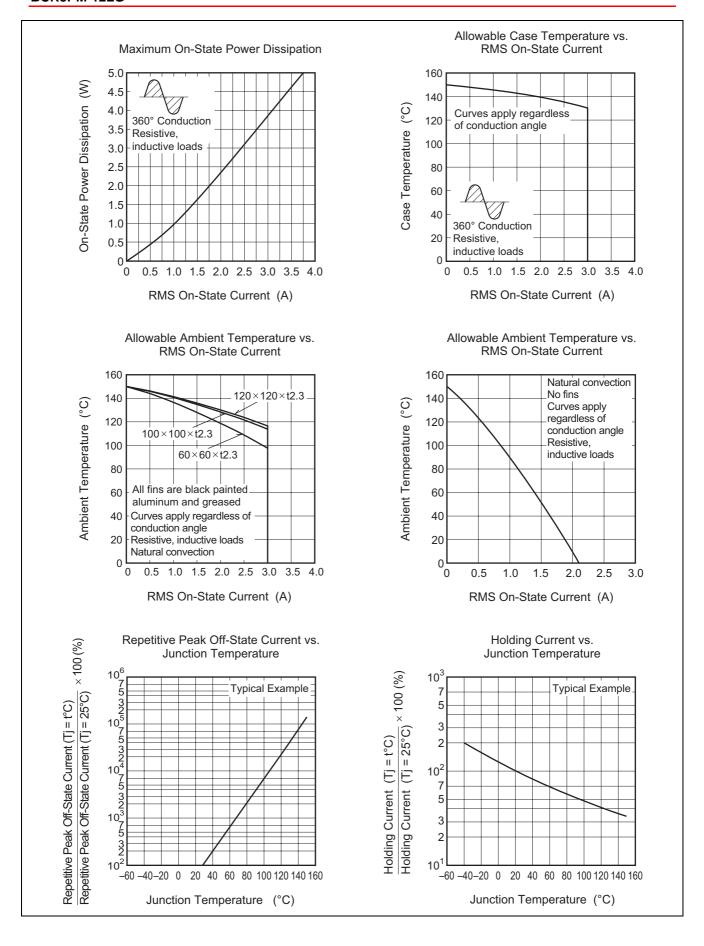
Notes: 2. Measurement using the gate trigger characteristics measurement circuit.

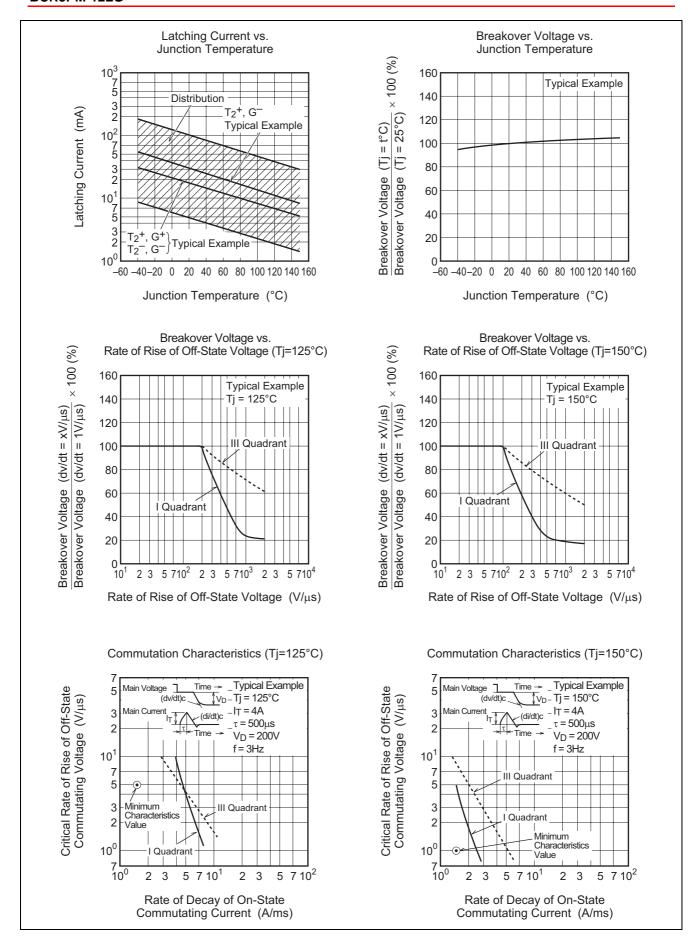
- 3. The contact thermal resistance $R_{th\,(j\text{-}c)}$ in case of greasing is 0.5°C/W.
- 4. Test conditions of the critical-rate of rise of off-state commutation voltage is shown in the table below.

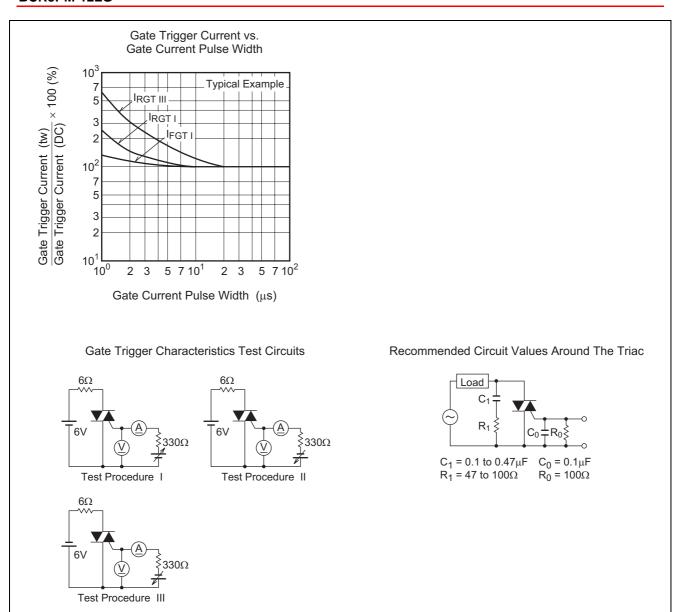
Test conditions	Commutating voltage and current waveforms (inductive load)		
1. Junction temperature Tj = 125°C/150°C	Supply Voltage →Time		
2. Rate of decay of on-state commutating current (di/dt)c = -1.5 A/ms	Main Current → (di/dt)c → Time		
3. Peak off-state voltage V _D = 400 V	Main Voltage Time		

Performance Curves

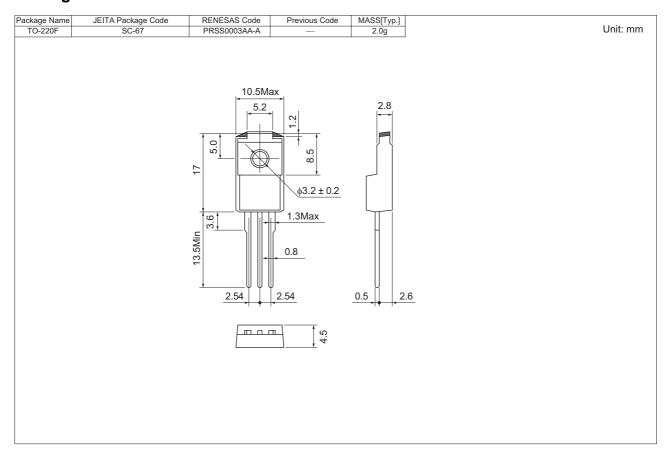








Package Dimensions



Order Code

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Straight type	Vinyl sack	100	Type name	BCR3PM-12LG
Lead form	Plastic Magazine (Tube)	50	Type name – Lead forming code	BCR3PM-12LG-A8

Note: Please confirm the specification about the shipping in detail.

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- Renesas lechnology Corp. Sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan Notes:

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